

L Number	Hits	Search Text	DB	Time stamp
6	1	372/20.ccls. and ( reflector ) and "90" near3 reflection	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:28
9	315	372/20.ccls. and ( reflector ) and reflection	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:35
10	537	etched adj3 mirror	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:36
11	393	etched adj3 mirror and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:36
12	44	etched adj3 mirror and semiconductor and polymer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:36
14	33	etched adj3 mirror and semiconductor and polymer and (silicon or glass)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:37
16	6	etched adj3 mirror and semiconductor and polymer and silicon and nickel and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:50
17	5	etched adj3 mirror and semiconductor and polymer and silicon and nickel and dielectric and MEM	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 18:27
-	468	372/20.ccls. and (tun\$3 adj3 laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:52
-	16	372/20.ccls. and (tun\$3 adj3 laser and edge near3 emitting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 09:39
-	1093	372/20.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 09:51
-	652	372/20.ccls. and ( tuning or tunable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 09:58
-	133424	reflector or mirror and resonator and (cavity or length)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 09:59
-	128868	reflector or mirror and resonator and gain and active and (cavity or length) and (fix\$2 or mobile or movable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 10:00
-	128539	reflector or mirror and resonator and gain and active and (cavity or length) and (fixed or mobile or movable) and (tune or tunable or tuning) and laser and length	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 10:01
-	333	(reflector or mirror) and resonator and gain and active and (cavity or length) and (fixed or mobile or movable) and (tune or tunable or tuning) and laser and length	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 10:01

-	333	(reflector or mirror) and resonator and gain and active and (cavity or length) and (fixed or mobile or movable) and (tune or tunable or tuning) and laser and length	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 10:02
-	2217	fixed adj3 reflector	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:21
-	335	fixed adj3 reflector and (movable or tunable) adj3 reflector	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:22
-	23	fixed adj3 reflector and (movable or tunable) adj3 reflector and active and gain and length and (fixed adj3 reflector and (movable or tunable) adj3 reflector)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:23
-	24	fixed adj3 reflector and (movable or tunable) adj3 reflector and active and gain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:24
-	8990	resonant adj3 cavity	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:38
-	270	resonant adj3 cavity and tunable near3 laser and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:39
-	21	resonant adj3 cavity and tunable near3 laser and semiconductor and movable and active	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:40
-	29	resonant adj3 cavity and tunable near3 laser and semiconductor and movable	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:40
-	52	Arbore near3 Mark or Myers near3 Lawrence	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:48
-	1093	372/20.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 15:30
-	0	372/20.ccls. and (anti\$refelection adj3 surface)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 15:31
-	14061	(etch or etching) and (polymer and air)	USPAT; US-PGPUB; DERWENT	2002/12/06 16:45
-	72	(etch or etching) and (polymer and air)and (MEM )	USPAT; US-PGPUB; DERWENT	2002/12/06 16:45
-	467	(etch or etching) and (polymer and air and semiconductor) and (MEM )	USPAT; US-PGPUB; DERWENT	2002/12/06 16:52
-	460	(etch or etching) and (polymer and air and semiconductor) and (MEM )and substrate	USPAT; US-PGPUB; DERWENT	2002/12/06 16:53
-	6	(etch or etching) and (polymer and air and semiconductor) and (MEM )and substrate and gain near3 medium and active and mirror	USPAT; US-PGPUB; DERWENT	2002/12/06 16:53
-	7	(etch or etching) and (polymer and air and semiconductor) and (MEM )and substrate and gain near3 medium	USPAT; US-PGPUB; DERWENT	2002/12/06 16:54
-	11	Jacquet near2 Joel	USPAT; US-PGPUB; DERWENT	2002/12/06 16:54